Number	T 37		Control Control		l m ·
Second S					
2 6926 laser near3 chip\$3 EPO, JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPAT; U	T	32919	semiconductor with (light near3 emitt\$3)		2003/01/09 18:27
DERMENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J			•	1	
TEM TDB					
2 6926 laser near3 chip\$3 1224 (semiconductor with (light near3 emit\$3)) 6 (laser near3 chip\$3) 1224 (semiconductor with (light near3 emit\$3)) 6 (laser near3 chip\$3) 123				DERWENT;	
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Semiconductor with (light near3 emitt\$3) Semiconductor with (lig	2	6926	laser near3 chip\$3	USPAT;	2003/01/09 18:28
1224 (semiconductor with (light near3 emitt\$3))			•	US-PGPUB:	
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1224 (semiconductor with (light near3 emitt\$3))				1	
\$\frac{\cappa}{\cappa}\$ \text{ (laser near3 chip\$3)} (US-PGPUB; EPC; JPC; DERWENT; IBM_TDB USPAT; US-PGPUB; emitt\$3)) & (laser near3 chip\$3)) & (mount near3 member) \text{ (((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & (mount near3 member)) & high\$3 & (thermal near3 expansion near3 coefficient) \text{ ((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & laser near3 chip\$3) & high\$3 & (thermal near3 expansion near3 emitt\$3)) & laser near3 chip\$3) & high\$3 & (thermal near3 expansion near3 emitt\$3) & laser near3 chip\$3) & high\$3 & (thermal near3 expansion near3 emitt\$3) & laser near3 chip\$3) & high\$3 & (thermal near3 expansion near3 emitt\$3) & laser near3 chip\$3) & high\$3 & (thermal near3 expansion near3 emitt\$3) & laser near3 chip\$3) & high\$3 & (thermal near3 expansion near3 emitt\$3) & laser near3 chip\$3) & high\$3 & (thermal near3 expansion near3 emitt\$3) & laser near3 chip\$3) & laser near3 ch	2	1224	/somiconductor with /light noing omittes)		2002/01/00 18-30
15	3	1224	(Semiconductor with (light hears emitt\$3))		2003/01/09 18:30
15			& (Laser nears cnipss)		
TBM_TDB					
15				DERWENT;	
emitt\$3)) & (laser near3 chip\$3)) & (mount near3 member)					
emitt\$3)) & (laser near3 chip\$3)) & (mount near3 member)	4	15	((semiconductor with (light near3	USPAT;	2003/01/09 18:33
Near3 member EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			emitt\$3)) & (laser near3 chip\$3)) & (mount	US-PGPUB;	
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emitt\$3)) & (laser near3 chip\$3)) & (mount near3 member)) & high\$3 & (thermal near3 expansion near3 coefficient) 88 ((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 & EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; IBO; IBO; IBO; IBO; IBO; IBO; IBO; IB	5	Δ	(((semiconductor with (light near3		2003/01/09 18:43
near3 member)) & high\$3 & (thermal near3 expansion near3 coefficient) 88 ((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-FGPUB; EPO; JPO; DERWENT; IBM TDB US-FGPUB; EPO; JPO; DERWENT; IBM TDB US-FAT; US-FGPUB; EPO; JPO; EPO		3		1	2003/01/09 18:43
expansion near3 coefficient)					
Second conductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 coefficient) Second coefficient) Coeffici					
Second conductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; Same surfac\$3) & ((laser near3 chip\$3)) & high\$3 EPO; JPO; DERWENT; Same surfac\$3) & ((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 EPO; JPO; DERWENT; Same surfac\$3)) & substrat\$3 US-PGPUB; EPO; JPO; DERWENT; Same surfac\$3)) & substrat\$3 USPĀT; US-PGPUB; EPO; JPO; DERWENT; Same surfac\$3)) & substrat\$3 USPĀT; US-PGPUB; EPO; JPO; DERWENT; Same surfac\$3)) & substrat\$3 USPĀT; US-PGPUB; EMITTEDB USPĀT; US-PGPUB; EMITTED			expansion nears coefficient)		
emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 coefficient) 16 (((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3)) & (layer\$3 with stack\$3) (semitt\$3)) & (layer\$3 with stack\$3) (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3)) & (layer\$3 with stack\$3) (semitt\$3)) & seme surfac\$3)) & substrat\$3 (semitt\$3)) & substrat\$3 (semitt\$3)) & substrat\$3 (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3) (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3) (semitt\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3) & (laser near3 chip\$3)) & (laser near3 chip\$3)) & high\$3 (semitt\$3) & (laser near3 chip\$3)) & (laser near3 chi		00	1,, , , , , , , , , , , , , , , , , , ,		
<pre>6 (thermal near3 expansion near3 coefficient) 7 16 (((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB;</pre>	ט	88			2003/01/09 18:41
coefficient) 16 (((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (SPAT; US-PGPUB; EPO; JPO; Coefficient)) & ((layer\$3 with stack\$3) EPO; JPO; DERWENT; Same surfac\$3) 8 16 ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (SPAT; US-PGPUB; EPO; JPO; DERWENT; EMITT\$3)) & (laser near3 chip\$3)) & high\$3 (SPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; Same surfac\$3)) & substrat\$3 (SPAT; US-PGPUB; EPO; JPO; DERWENT; Same surfac\$3)) & substrat\$3 (((((semiconductor with (light near3 emitt\$3))) & high\$3 (((((semiconductor with (light near3 emitt\$3))) & high\$3 (US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; EMITT\$3)) & (((((semiconductor with (light near3 emitt\$3))) & high\$3 (US-PGPUB; EPO; JPO; EPO;					
TBM TDB (((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3				EPO; JPO;	
16 (((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) EPO; JPO; DERWENT; same surfac\$3) ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) EPO; JPO; DERWENT; same surfac\$3)) & substrat\$3 (layer\$3 with stack\$3) EPO; JPO; same surfac\$3)) & substrat\$3 ((((semiconductor with (light near3 emitt\$3)) & substrat\$3 ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (US-PGPUB; emitt\$3)) & (laser near3 chip\$3)) & high\$3 (US-PGPUB; EPO; JPO; EPO; JPO;			coefficient)	DERWENT;	
16 (((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) EPO; JPO; DERWENT; same surfac\$3) ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) EPO; JPO; DERWENT; same surfac\$3)) & substrat\$3 (layer\$3 with stack\$3) EPO; JPO; same surfac\$3)) & substrat\$3 ((((semiconductor with (light near3 emitt\$3)) & substrat\$3 ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (US-PGPUB; emitt\$3)) & (laser near3 chip\$3)) & high\$3 (US-PGPUB; EPO; JPO; EPO; JPO;				IBM TDB	
emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) DERWENT; same surfac\$3) ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) DERWENT; same surfac\$3)) & substrat\$3 US-PGPUB; & (thermal near3 expansion near3 COERWENT; same surfac\$3)) & substrat\$3 US-PGPUB; emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 US-PGPUB; & (7	16	(((semiconductor with (light near3		2003/01/09 18:47
& (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) Berwent; same surfac\$3) ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 coefficient)) & ((layer\$3 with stack\$3) coefficient)) & ((layer\$3 with stack\$3) same surfac\$3)) & substrat\$3 ((((semiconductor with (light near3 emitt\$3)) & substrat\$3 ((((semiconductor with (light near3 emitt\$3)) & ligh\$3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 EPO; JPO; DERWENT; IBM TDB USPAT; USPAT; USPAT; EPO; JPO; EPO; JPO;			emitt\$3)) & (laser near3 chip\$3)) & high\$3		
coefficient)) & ((layer\$3 with stack\$3) Berwent; same surfac\$3) ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) coefficient)) & ((layer\$3 with stack\$3) same surfac\$3)) & substrat\$3 ((((semiconductor with (light near3 emitt\$3)) & high\$3 ((((semiconductor with (light near3 emitt\$3)) & laser near3 chip\$3)) & high\$3 (thermal near3 expansion near3 DERWENT; IBM TDB US-PGPUB; US-PGPUB; Emitt\$3)) & (laser near3 chip\$3)) & high\$3 EPO; JPO;					
same surfac\$3) ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (US-PGPUB; EPO; JPO; coefficient)) & ((layer\$3 with stack\$3) DERWENT; same surfac\$3)) & substrat\$3 (((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 (US-PGPUB; emitt\$3)) & (laser near3 chip\$3)) & high\$3 (US-PGPUB; & (thermal near3 expansion near3 EPO; JPO;					
8 16 ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; EPO; JPO; coefficient)) & ((layer\$3 with stack\$3) DERWENT; same surfac\$3)) & substrat\$3 IBM TDB ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 EPO; JPO;	,				
emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; EPO; JPO; coefficient)) & ((layer\$3 with stack\$3) DERWENT; same surfac\$3)) & substrat\$3 IBM_TDB (((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 EPO; JPO;	8	16		_	2003/01/00 10.57
& (thermal near3 expansion near3 coefficient)) & ((layer\$3 with stack\$3) DERWENT; same surfac\$3)) & substrat\$3 IBM TDB (((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 EPO; JPO;		10	emitt\$3\) ((lacor near) chin\$3\\ (hi~h¢2	1	2003/01/09 18:5/
coefficient)) & ((layer\$3 with stack\$3) DERWENT; same surfac\$3)) & substrat\$3 10 15 ((((semiconductor with (light near3 emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 EPO; JPO;					
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emitt\$3)) & (laser near3 chip\$3)) & high\$3 US-PGPUB; & (thermal near3 expansion near3 EPO; JPO;	10				
& (thermal near3 expansion near3 EPO; JPO;	10	15		USPAT;	2003/01/09 18:59
				US-PGPUB;	
coefficient()				EPO; JPO;	
Coefficient)) & ((layer\$3 with stack\$3) DERWENT;			coefficient)) & ((layer\$3 with stack\$3)	DERWENT;	
same surfac\$3)) & substrat\$3) & nitrid\$3 IBM TDB					